

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRFR9N20D, IIRFR9N20D

FEATURES

- Static drain-source on-resistance: Ros(on)≤380mΩ
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

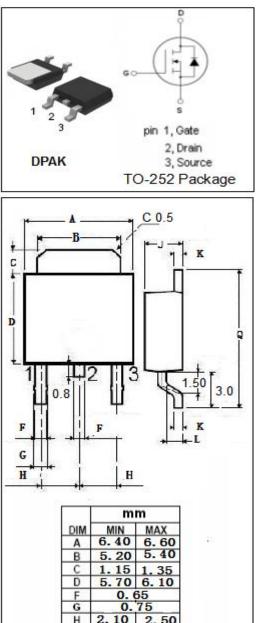
· High frequency DC-DC converters

• ABSOLUTE MAXIMUM RATINGS(T=25°C)

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SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage 200		V				
V _{GS}	Gate-Source Voltage ±30		V				
ID	Drain Current-Continuous 9.4		А				
I _{DM}	Drain Current-Single Pulsed	38	А				
PD	Total Dissipation @T _c =25°C	86	W				
Tj	Max. Operating Junction Temperature	175	°C				
T _{stg}	Storage Temperature	-55~175	°C				

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(j-c)	Channel-to-case thermal resistance	1.75	°C/W
Rth(j-a)	Rth(j-a) Channel-to-ambient thermal resistance		℃ /W



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0

2.10

0.40

0.90

9.90

50

40

10

0.60



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	200			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =250 µ A	3		5.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =5.6A			380	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =200V; V _{GS} = 0V			25	μA
V _{SD}	Diode forward voltage	I _s =5.6A, V _{GS} = 0V			1.3	V

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